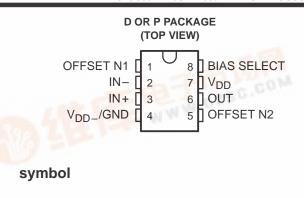
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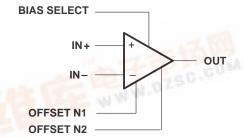
捷多邦 TEO251 打 TEO251 A小 时也 C251 B, TLC 251 Y LinCMOS[™] PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS SLOS001E - JULY 1983 - REVISED AUGUST 1994

- Wide Range of Supply Voltages 1.4 V to 16 V
- True Single-Supply Operation
- **Common-Mode Input Voltage Range Includes the Negative Rail**
- Low Noise . . . 30 nV/ \sqrt{Hz} Typ at 1 kHz (High Bias)
- ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015.1 DZSC.COM

description

The TLC251C, TLC251AC, and TLC251BC are low-cost, low-power programmable operational amplifiers designed to operate with single or dual supplies. Unlike traditional metal-gate CMOS operational amplifiers, these devices utilize Texas Instruments silicon-gate LinCMOS[™] process, giving them stable input offset voltages without sacrificing the advantages of metal-gate CMOS.





This series of parts is available in selected grades of input offset voltage and can be nulled with one external potentiometer. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this family is ideally suited for battery-powered or energy-conserving applications. A bias-select pin can be used to program one of three ac performance and power-dissipation levels to suit the application. The series features operation down to a 1.4-V supply and is stable at unity gain.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in a degradation of the device parametric performance.

Because of the extremely high input impedance and low input bias and offset currents, applications for the TLC251C series include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOS™ operational amplifiers without the power penalties of traditional bipolar devices. Remote and inaccessible equipment applications are possible using the low-voltage and low-power capabilities of the TLC251C series.

In addition, by driving the bias-select input with a logic signal from a microprocessor, these operational amplifiers can have software-controlled performance and power consumption. The TLC251C series is well suited to solve the difficult problems associated with single battery and solar cell-powered applications.

The TLC251C series is characterized for operation from 0°C to 70°C.

	and the second se			
	Mismax	PACKAGE	DEVICES	
TA	VIOMAX AT 25°C 10 mV TLC251CD	SMALL OUTLINE (D)	PLASTIC DIP (P)	CHIP FORM (Y)
A. Service	10 mV	TLC251CD	TLC251CP	TLC251Y
0°C to 70°C	5 mV	TLC251ACD	TLC251ACP	—
	2 mV	TLC251BCD	TLC251BCP	—

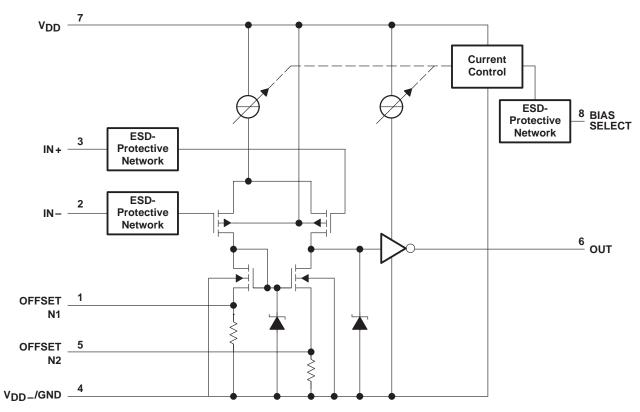
AVAILABLE OPTIONS

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC251CDR). Chips are tested at 25°C.

tinCMOS is a trademark of Texas Instruments Incorporated.



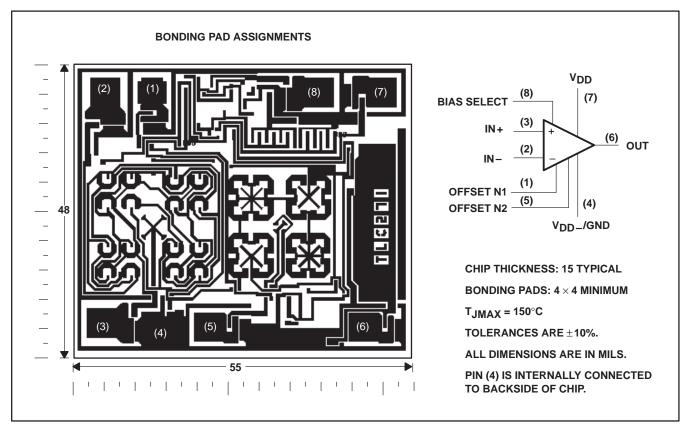
schematic





TLC251Y chip information

These chips, properly assembled, display characteristics similar to the TLC251C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1)	18 V
Differential input voltage, VID (see Note 2)	
Input voltage range, V _I (any input)	
Duration of short circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD}_/GND.

- 2. Differential voltages are at IN+ with respect to IN-.
- 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW

recommended operating conditions

		MI	MAX	UNIT
Supply voltage, V _{DD}		1.	4 16	V
	$V_{DD} = 1.4 V$		0 0.2	
	$V_{DD} = 5 V$	-0.	2 4	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.	2 9	1 [×]
	V _{DD} = 16 V	-0.	2 14]
Operating free-air temperature, TA			0 70	°C
Bias-select voltage		5	See Applic Informat	



HIGH-BIAS MODE

electrical characteristics at specified free-air temperature

					т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	т _А †	v	DD = 5 \	/	V) D = 10	v	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		TI 00540		25°C		1.1	10		1.1	10	
		TLC251C	V _O = 1.4 V,	Full range			12			12	
	have the first sector and		$V_{IC} = 0 V,$	25°C		0.9	5		0.9	5	
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 kΩ	25°C		0.34	2		0.39	2	
		TLC251BC		Full range			3			3	
αΛΙΟ	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.8			2		μV/°C
	lanut offerst summert (s		$V_{O} = V_{DD}/2,$	25°C		0.1			0.1		- 4
IIO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	pА
1	Innut biog ourrest (og	o Noto ()	$V_{O} = V_{DD}/2,$	25°C		0.6			0.7		~ ^
IВ	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	рА
	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)			Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	3.8		8	8.5		
∨он	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 10 \text{ k}\Omega$	0°C	3	3.8		7.8	8.5		V
				70°C	3	3.8		7.8	8.4		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			10L - 0	70°C		0	50		0	50	
	1	·	D 4010	25°C	5	23		10	36		
AVD	Large-signal different amplification	iai voitage	$R_L = 10 k\Omega$, See Note 6	0°C	4	27		7.5	42		V/mV
				70°C	4	20		7.5	32		
				25°C	65	80		65	85		
CMRR	Common-mode rejec	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	84		60	88		dB
				70°C	60	85		60	88		
	Supply-voltage reject	ion ratio	$V_{DD} = 5 V + 0.10 V$	25°C	65	95		65	95		
^k SVR	Supply-voltage reject (ΔVDD/ΔVIO)		$V_{DD} = 5 V \text{ to } 10 V,$ $V_{O} = 1.4 V$	0°C	60	94		60	94		dB
				70°C	60	96		60	96		
II(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = 0$	25°C		-1.4			-1.9		μΑ
			$V_{O} = V_{DD}/2,$	25°C		675	1600		950	2000	
IDD	Supply current		$V_{IC} = V_{DD}/2,$ No load	0°C		775	1800		1125	2200	μA
+			no luau	70°C		575	1300		750	1700	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 \text{ V}$, $V_{O} = 0.25 \text{ V}$ to 2 V; at $V_{DD} = 10 \text{ V}$, $V_{O} = 1 \text{ V}$ to 6 V.



HIGH-BIAS MODE

operating characteristics, $V_{DD} = 5 V$

	PARAMETER	1	EST CONDITIO	DNS	тд	TLC251 TL	C, TLC2 C251B0		UNIT
						MIN	TYP	MAX	
					25°C		3.6		
				V _{I(PP)} = 1 V	0°C		4		
SR	Slow rate at unity gain	$P_{\rm L} = 10 \mathrm{kO}$	$C_{1} = 20 \text{ pE}$		70°C		3		\//uo
SK	Slew rate at unity gain	$K_{L} = 10 \text{ Ksz},$	C _L = 20 pF		25°C		2.9		V/μs
				V _{I(PP)} = 2.5 V	0°C		3.1		
					70°C		2.5		
٧ _n	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		25		nV/√Hz
					25°C		320		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 10 \ k\Omega$	0°C		340		kHz
					70°C		260		
					25°C		1.7		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		0°C		2		MHz
					70°C		1.3		
					25°C		46°		
∮m	Phase margin	V _I = 10 mV,	f = B ₁ ,	C _L = 20 pF	0°C		47°		
					70°C		44°		

operating characteristics, V_{DD} = 10 V

	PARAMETER	т	EST CONDITIO	DNS	Тд	TLC251 TL	C, TLC2 C251B0		UNIT
						MIN	TYP	MAX	
					25°C		5.3		
				V _{I(PP)} = 1 V	0°C		5.9		
SR	Slew rate at unity gain	$P_{\rm L} = 10 \mathrm{ko}$	C _L = 20 pF		70°C		4.3		V/µs
SK	Siew fale at unity gain	$K_{L} = 10 \text{ Ksz},$	CL = 20 pF		25°C		4.6		v/μs
				VI(PP) = 5.5 V	0°C		5.1		
					70°C		3.8		
V _n	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		25		nV/√Hz
					25°C		200		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 10 \ k\Omega$	0°C		220		kHz
					70°C		140		
					25°C		2.2		
В ₁	Unity-gain bandwidth	V _I = 10 mV,	$C_L = 20 \text{ pF}$		0°C		2.5		MHz
					70°C		1.8		
					25°C		49°		
∮m	Phase margin	V _I = 10 mV,	$f = B_1,$	C _L = 20 pF	0°C		50°		
					70°C		46°		



MEDIUM-BIAS MODE

electrical characteristics at specified free-air temperature

					т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	т _А †	v	DD = 5 \	/	V	OD = 10	V	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		-		25°C		1.1	10		1.1	10	
		TLC251C		Full range			12			12	
			V _O = 1.4 V, V _{IC} = 0 V,	25°C		0.9	5		0.9	5	.,
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 kΩ	25°C		0.34	2		0.39	2	
		TLC251BC		Full range			3			3	
αΛΙΟ	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.7			2.1		μV/°C
			$V_{O} = V_{DD}/2,$	25°C		0.1			0.1		
IIO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	рА
			$V_{O} = V_{DD}/2,$	25°C		0.6			0.7		
IB	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	pА
Mar	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)			Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	3.9		8	8.7		
∨он	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 10 \text{ k}\Omega$	0°C	3	3.9		7.8	8.7		V
				70°C	3	4		7.8	8.7		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			10L = 0	70°C		0	50		0	50	
				25°C	25	170		25	275		
AVD	Large-signal different amplification	ial voltage	$R_L = 10 k\Omega$, See Note 6	0°C	15	200		15	320		V/mV
	ampinoation			70°C	15	140		15	230		
				25°C	65	91		65	94		
CMRR	Common-mode reject	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	91		60	94		dB
				70°C	60	92		60	94		
				25°C	70	93		70	93		
k SVR	Supply-voltage reject (ΔVDD/ΔVIO)	ion ratio	$V_{DD} = 5 V \text{ to } 10 V,$ $V_{O} = 1.4 V$	0°C	60	92		60	92		dB
			VU - 1.4 V	70°C	60	94		60	94		
II(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = V_{DD}/2$	25°C		-130			-160		nA
/			$V_{O} = V_{DD}/2,$	25°C		105	280		143	300	
IDD	Supply current		$V_{IC} = V_{DD}/2$,	0°C		125	320		173	400	μA
			No load	70°C		85	220		110	280	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 V$, $V_{O} = 0.25 V$ to 2 V; at $V_{DD} = 10 V$, $V_{O} = 1 V$ to 6 V.



MEDIUM-BIAS MODE

operating characteristics, $V_{DD} = 5 V$

	PARAMETER	т	EST CONDITIC	ONS	тд	TLC251 TL	C, TLC2 .C251B0		UNIT
						MIN	TYP	MAX	
					25°C		0.43		
				VI(PP) = 1 V	0°C		0.46		
SR	Slew rate at unity gain	R _L = 100 kΩ,	$C_{1} = 20 \text{ pE}$		70°C		0.36		V/µs
	Siew fale at unity gain	$ \mathbf{K} = 100 \text{ ksz},$	CL = 20 pr		25°C		0.40		ν/μ5
				V _{I(PP)} = 2.5 V	0°C		0.43		
					70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		32		nV/√Hz
					25°C		55		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$	$C_{L} = 20 \text{ pF},$	$R_L = 100 \text{ k}\Omega$	0°C		60		kHz
					70°C		50		
					25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	$C_L = 20 \text{ pF}$		0°C		600		kHz
					70°C		400		
					25°C		40°		
φm	Phase margin	V _I = 10 mV,	$f = B_1,$	C _L = 20 pF	0°C		41°		
					70°C		39°		

operating characteristics, V_{DD} = 10 V

	PARAMETER	т	EST CONDITIC	ONS	TA	TLC251 TL	C, TLC2 .C251B0		UNIT
						MIN	TYP	MAX	
					25°C		0.62		
				V _{I(PP)} = 1 V	0°C		0.67		
SR	Slew rate at unity gain	R _L = 100 kΩ,	$C_{1} = 20 \text{ pE}$		70°C		0.51		V/µs
	Siew rate at unity gain	$ \mathbf{K} = 100 \text{ ksz},$	CL = 20 pr		25°C		0.56		ν/μ5
				VI(PP) = 5.5 V	0°C		0.61		
					70°C		0.46		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		32		nV/√Hz
					25°C		35		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$	CL = 20 pF,	$R_L = 100 \text{ k}\Omega$	0°C		40		kHz
					70°C		30		
					25°C		635		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		0°C		710		kHz
					70°C		510		
					25°C		43°		
φm	Phase margin	V _I = 10 mV,	$f = B_1$,	CL = 20 pF	0°C		44°		
					70°C		42°		



LOW-BIAS MODE

electrical characteristics at specified free-air temperature

					Т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	тд†	v	DD = 5 \	/	٧Ľ) D = 10	V	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		-		25°C		1.1	10		1.1	10	
		TLC251C		Full range			12			12	
.,		TI 005440	V _O = 1.4 V, V _{IC} = 0 V,	25°C		0.9	5		0.9	5	.,
VIO	Input offset voltage	TLC251AC	R _S = 50 Ω,	Full range			6.5			6.5	mV
			R _L = 10 MΩ	25°C		0.24	2		0.26	2	
		TLC251BC		Full range			3			3	
αΛΙΟ	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.1			1		μV/°C
			$V_{O} = V_{DD}/2,$	25°C		0.1			0.1		
IIO	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	pА
1	lanut biog summant (as	a Nata ()	$V_{O} = V_{DD}/2,$	25°C		0.6			0.7		- 4
IB	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	рА
.,	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)	Ū		Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	4.1		8	8.9		
∨он	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 1 \text{ M}\Omega$	0°C	3	4.1		7.8	8.9		V
				70°C	3	4.2		7.8	8.9		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			10L = 0	70°C		0	50		0	50	
	1	- 1 II	D (110	25°C	50	520		50	870		
AVD	Large-signal different amplification	iai voitage	$R_L = 1 M\Omega$, See Note 6	0°C	50	700		50	1030		V/mV
				70°C	50	380		50	660		
				25°C	65	94		65	97		
CMRR	Common-mode rejec	tion ratio	$V_{IC} = V_{ICR}min$	0°C	60	95		60	97		dB
				70°C	60	95		60	97		
	Supply voltage relast	ion ratio		25°C	70	97		70	97		
^k SVR	Supply-voltage reject (ΔVDD/ΔVIO)	IUITALIU	$V_{DD} = 5 V \text{ to } 10 V,$ $V_{O} = 1.4 V$	0°C	60	97		60	97		dB
	-		Ŭ	70°C	60	98		60	98		
II(SEL)	Input current (BIAS S	ELECT)	V _{I(SEL)} = V _{DD}	25°C		65			95		nA
			$V_{O} = V_{DD}/2,$	25°C		10	17		14	23	
IDD	Supply current		$V_{IC} = V_{DD}/2$,	0°C		12	21		18	33	μA
			No load	70°C		8	14		11	20	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.

6. At $V_{DD} = 5 \text{ V}$, $V_{O} = 0.25 \text{ V}$ to 2 V; at $V_{DD} = 10 \text{ V}$, $V_{O} = 1 \text{ V}$ to 6 V.



LOW-BIAS MODE

operating characteristics, $V_{DD} = 5 V$

	PARAMETER	т	EST CONDITIC	ONS	ТА	TLC251 TL	C, TLC2 .C251B(UNIT
						MIN	TYP	MAX	
					25°C		0.03		
				VI(PP) = 1 V	0°C		0.04		
SR	Slow rate at upity gain	$\mathbf{P}_{1} = 1 \mathrm{MO}$	$C_{1} = 20 \text{ pE}$		70°C		0.03		V/ue
SK	Slew rate at unity gain	$R_{L} = 1 M\Omega,$	C _L = 20 pF		25°C		0.03		V/µs
				V _{I(PP)} = 2.5 V	0°C		0.03		
					70°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		68		nV/√Hz
					25°C		5		
ВОМ	Maximum output-swing bandwidth	$V_{O} = V_{OH},$	C _L = 20 pF,	$R_L = 1 M\Omega$	0°C		6		kHz
					70°C		4.5		
					25°C		85		
B ₁	Unity-gain bandwidth	Vj = 10 mV,	$C_L = 20 \text{ pF}$		0°C		100		kHz
					70°C		65		
					25°C		34°		
∮m	Phase margin	V _I = 10 mV,	$f = B_1,$	C _L = 20 pF	0°C		36°		
					70°C		30°		

operating characteristics, $V_{DD} = 10 V$

PARAMETER		т	TA	TLC251C, TLC251AC, TLC251BC		UNIT			
							TYP	MAX	
					25°C		0.05		
				VI(PP) = 1 V	0°C		0.05		
SR	Slew rate at unity gain	$R_{I} = 1 M\Omega,$	C _L = 20 pF		70°C		0.04		V/µs
SK	Siew fale at unity gain	$K_{L} = 1 \text{ IVIS2},$	CL = 20 pr		25°C		0.04		v/μs
				V _{I(PP)} = 5.5 V	0°C		0.05		
					70°C		0.04		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω	_	25°C		68		nV/√Hz
					25°C		1		
Вом	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF,	$R_L = 1 M\Omega$	0°C		1.3		kHz
					70°C		0.9]
					25°C		110		
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		0°C		125		kHz
					70°C		90		
					25°C		38°		
∮m	Phase margin	V _I = 10 mV,	$f = B_1$,	C _L = 20 pF	0°C		40°		
					70°C		34°		



electrical characteristics at specified free-air temperature, V_{DD} = 1.4 V

PARAMETER		R	TEST CONDITIONS [†]		т _А ‡	BIAS	TLC251C, TLC251AC, TLC251BC		UNIT	
						MIN	TYP	MAX	1	
		TLC251C			25°C	4.004			10	
		1202510			Full range	Any			12	
VIO	Input offset	TLC251AC	V _O = 0.2 V,	R _S = 50 Ω	25°C	Any			5	mV
10	voltage	TLOZSTAC	VO = 0.2 V,	NS = 30.32	Full range	Any			6.5	IIIV
		TLC251BC			25°C	Any			2	
		12020100			Full range	, (i) y			3	
αΛΙΟ	Average temp coefficient of i voltage				25°C to 70°C	Any		1		μV/°C
lie	Input offset current		V _O = 0.2 V		25°C	Any		1		pА
IIO	input onset ct	Inent	VO = 0.2 V		Full range				300	рА
IIB	Input bias current		V _O = 0.2 V		25°C	Any		1		pА
ΊΒ		Torit	VO = 0.2 V		Full range	Ally			600	рл
VICR	Common-moo voltage range				25°C	Any	0 to 0.2			V
VOM	Peak output v swing§	oltage	V _{ID} = 100 mV		25°C	Any	450	700		mV
A. (5)	Large-signal differential		$V_{O} = 100 \text{ to } 300 \text{ mV},$	$P_{0} = 50.0$	25°C	Low		20		
AVD	AVD voltage amplification		$v_0 = 100 to 300 mV,$	1/2 = 30.75	23.0	High		10		
CMRR	Common-moo ratio	de rejection	$R_S = 50 \Omega$, $V_{IC} = V_{ICR}min$	V _O = 0.2 V,	25°C	Any	60	77		dB
	Supply currer	+	V _O = 0.2 V,	No load	25°C	Low		5	17	μA
IDD		it.	$v_{\rm O} = 0.2 \text{ v},$ indicad	23.0	High		150	190	μΛ	

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following values: for low bias, RL = 1 MΩ, for medium bias,

 $R_L = 100 \text{ k}\Omega$, and for high bias, $R_L = 10 \text{ k}\Omega$.

[‡]Full range is 0°C to 70°C.

The output swings to the potential of V_{DD}-/GND.

operating characteristics, V_{DD} = 1.4 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT	
				MIN	TYP	MAX		
в.			Low		12		kHz	
B ₁	Unity-gain bandwidth	C _L = 100 pF	High		12		ri IZ	
SR			Low		0.001		N/we	
SK	Slew rate at unity gain	See Figure 1	High		0.1		V/µs	
	Overshoot factor	See Figure 1	Low		35%			
	Overshoot factor	See Figure 1	High		30%			



electrical characteristics, V_{DD} = 5 V, T_A = 25°C

			TLC251Y									
	PARAMETER	TEST CONDITIONS	HIGH-BIAS MODE			MEDIUM-BIAS MODE			LOW-BIAS MODE			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage			1.1	10		1.1	10		1.1	10	mV
αNO	Average temperature coefficient of input offset voltage			1.8			1.7			1.1		μV/°C
IIO	Input offset current (see Note 4)	$V_{O} = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.1			0.1			0.1		pА
I _{IB}	Input bias current (see Note 4)	$V_{O} = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.6			0.6			0.6		pА
VICR	Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		V
VOH	High-level output voltage	V _{ID} = 100 mV, R _L †	3.2	3.8		3.2	3.9		3.2	4.1		V
V _{OL}	Low-level output voltage	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$		0	50		0	50		0	50	mV
A _{VD}	Large-signal differential voltage amplification	V _O = 0.25 V, RL [†]	5	23		25	170		50	480		V/mV
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min$	65	80		65	91		65	94		dB
^k SVR	Supply-voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	$V_{DD} = 5 V \text{ to } 10 V,$ $V_{O} = 1.4 V$	65	95		70	93		70	97		dB
II(SEL)	Input current (BIAS SELECT)	$V_{I(SEL)} = V_{DD}/2$		-1.4			-0.13			0.065		μA
I _{DD}	Supply current	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2,$ No load		675	1600		105	280		10	17	μΑ

[†] For high-bias mode, $R_L = 10 \text{ k}\Omega$; for medium-bias mode, $R_L = 100 \text{ k}\Omega$; and for low-bias mode, $R_L = 1 \text{ M}\Omega$.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically. 5. This range also applies to each input individually.



TLC251, TLC251A, TLC251B, TLC251Y LinCMOS[™] PROGRAMMABLE LOW-POWER OPERATIONAL AMPLIFIERS

SLOS001E - JULY 1983 - REVISED AUGUST 1994

UNIT

V/µs

nV/√Hz

kHz

kHz

		TLC251Y																
PARAMETER		TEST CC	HIGH-BIAS MODE				DIUM-B MODE	IAS	LOW-BIAS MODE									
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX						
SR	Slew rate at	RL [†] ,	V _{I(PP)} = 1 V		3.6			0.43			0.03							
OIX	unity gain	C _L = 20 pF	VI(PP) = 2.5 V		2.9			0.40			0.03							
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25			32			68							
BOM	Maximum output swing bandwidth	$V_O = V_{OH},$ R _L = 10 k Ω	C _L = 20 pF,		320			55			4.5							
В ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF	1700		1700		1700		1700		1700 525		525			65	
φm	Phase margin	f = B ₁ , C _L = 20 pF	V _I = 10 mV,		46°			40°			34°							

orating characteristics $V_{--} = 5 V T_{+} = 25^{\circ}C$

[†] For high-bias mode, $R_L = 10 \text{ k}\Omega$; for medium-bias mode, $R_L = 100 \text{ k}\Omega$; and for low-bias mode, $R_L = 1 \text{ M}\Omega$.

PARAMETER MEASUREMENT INFORMATION

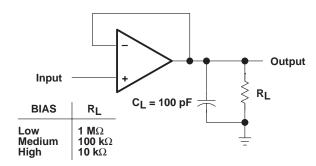


Figure 1. Unity-Gain Amplifier

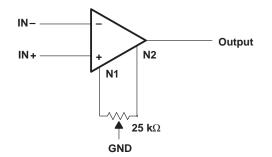


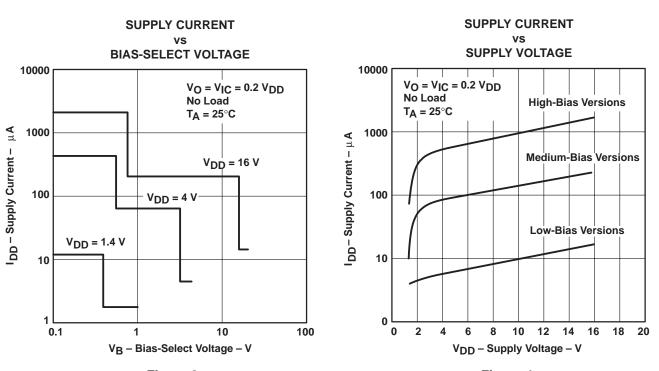
Figure 2. Input Offset Voltage Null Circuit

TYPICAL CHARACTERISTICS

Table of Graphs

IDD	Supply current	vs Bias-select voltage vs Supply voltage vs Free-air temperature	3 4 5				
		Low bias	vs Frequency	6			
AVD	Large-signal differential voltage amplification	Medium bias	vs Frequency	7			
		High bias	vs Frequency	8			
		Low bias	vs Frequency	6			
	Phase shift	Medium bias	vs Frequency	7			
		High bias	vs Frequency	8			

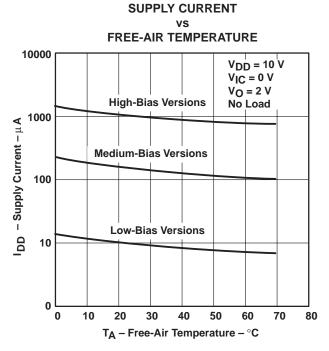




TYPICAL CHARACTERISTICS



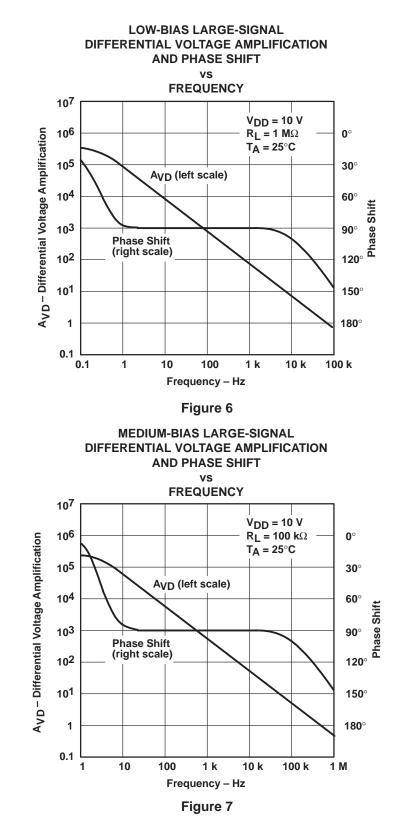
Figure 4





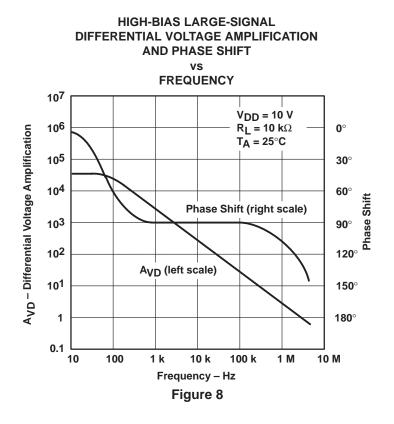


TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS



APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNPN structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifier supplies should be applied simultaneously with, or before, application of any input signals.



APPLICATION INFORMATION

using BIAS SELECT

The TLC251 has a terminal called BIAS SELECT that allows the selection of one of three I_{DD} conditions (10, 150, and 1000 μ A typical). This allows the user to trade-off power and ac performance. As shown in the typical supply current (I_{DD}) versus supply voltage (V_{DD}) curves (Figure 4), the I_{DD} varies only slightly from 4 V to 16 V. Below 4 V, the I_{DD} varies more significantly. Note that the I_{DD} values in the medium- and low-bias modes at V_{DD} = 1.4 V are typically 2 μ A, and in the high mode are typically 12 μ A. The following table shows the recommended BIAS SELECT connections at V_{DD} = 10 V.

BIAS MODE	AC PERFORMANCE	PERFORMANCE BIAS SELECT CONNECTION [†]	
Low	Low	V _{DD}	10 µA
Medium	Medium	0.8 V to 9.2 V	150 μA
High	High	Ground pin	1000 μA

[†] Bias selection may also be controlled by external circuitry to conserve power, etc. For information regarding BIAS SELECT, see Figure 3 in the typical characteristics curves.

[‡] For I_{DD} characteristics at voltages other than 10 V, see Figure 4 in the typical characteristics curves.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD} –/GND.

input offset nulling

The TLC251C series offers external offset null control. Nulling may be achieved by adjusting a 25-k Ω potentiometer connected between the offset null terminals with the wiper connected to the device V_{DD}_/GND pin as shown in Figure 2. The amount of nulling range varies with the bias selection. At an I_{DD} setting of 1000 μ A (high bias), the nulling range allows the maximum offset specified to be trimmed to zero. In low or medium bias or when the amplifier is used below 4 V, total nulling may not be possible for all units.

supply configurations

Even though the TLC251C series is characterized for single-supply operation, it can be used effectively in a split-supply configuration when the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

The user is cautioned that whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup, as well as excessive dc leakages.



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